## Introducing Asymmetry in a CMOS Latch to Obtain Inherent Power-On-Reset Behavior

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- $\triangleright$  We propose the use of asymmetry in a latch, turning its initial value into an well-determined state without the need of a reset.







 $\triangleright$  Mostly used in SRAM, but can be used in sequential circuits for ultra-low-power applications.







![](_page_7_Figure_4.jpeg)

Inverter transference

![](_page_8_Picture_0.jpeg)

![](_page_8_Figure_2.jpeg)

![](_page_8_Figure_3.jpeg)

![](_page_9_Picture_0.jpeg)

![](_page_9_Figure_2.jpeg)

![](_page_9_Figure_3.jpeg)

![](_page_9_Figure_4.jpeg)

![](_page_10_Picture_0.jpeg)

![](_page_10_Picture_2.jpeg)

## Process variations

![](_page_10_Figure_4.jpeg)

 $\blacktriangleright$  Montecarlo simulation: From 300 samples, *Q<sup>S</sup>* started with '0' in 144 samples and with '1' in 156 samples.

![](_page_11_Picture_0.jpeg)

![](_page_11_Picture_2.jpeg)

![](_page_11_Figure_3.jpeg)

 $\triangleright$  Can be observed in a transient noise simulation.

![](_page_12_Picture_0.jpeg)

![](_page_12_Picture_2.jpeg)

## Input devices

![](_page_12_Figure_4.jpeg)

- $\triangleright$  Unknown initial input voltages  $(R, S)$ .
- $\triangleright$  Different sizes or number of transistors in each side.
- $\triangleright$  Very difficult to predict at the design stage.

![](_page_13_Picture_0.jpeg)

## Proposed Asymmetry

![](_page_13_Figure_2.jpeg)

► Low-vt current  $\approx$  10X greater than regular transistors at  $V_{GS}$  = 0.

![](_page_14_Picture_0.jpeg)

![](_page_14_Picture_2.jpeg)

![](_page_14_Figure_3.jpeg)

![](_page_14_Figure_4.jpeg)

![](_page_15_Picture_0.jpeg)

![](_page_15_Picture_2.jpeg)

![](_page_15_Figure_3.jpeg)

![](_page_15_Figure_4.jpeg)

![](_page_16_Picture_0.jpeg)

![](_page_16_Figure_2.jpeg)

![](_page_16_Figure_3.jpeg)

![](_page_16_Figure_4.jpeg)

curves: 3 intercepts

![](_page_16_Figure_6.jpeg)

Solutions when Vdd varies from 0 to 1.2 V

![](_page_16_Figure_8.jpeg)

Zoom for Vdd values up to 100mV

![](_page_17_Picture_0.jpeg)

![](_page_17_Picture_2.jpeg)

![](_page_17_Figure_3.jpeg)

![](_page_17_Figure_4.jpeg)

![](_page_17_Figure_5.jpeg)

Power-On Reseted Flip-Flop

![](_page_18_Picture_0.jpeg)

![](_page_18_Picture_1.jpeg)

![](_page_18_Picture_2.jpeg)

![](_page_18_Figure_3.jpeg)

![](_page_18_Picture_4.jpeg)

![](_page_18_Figure_5.jpeg)

 $\triangleright$  *Q*<sub>*AM*</sub> was expected to start with '0'. Verified

Slide 11

![](_page_19_Picture_0.jpeg)

![](_page_19_Picture_1.jpeg)

![](_page_19_Picture_2.jpeg)

![](_page_19_Figure_3.jpeg)

![](_page_19_Picture_4.jpeg)

![](_page_19_Figure_5.jpeg)

<sup>I</sup> *QAM* was expected to start with '0'. Verified

<sup>I</sup> *QSM* was unpredicted at design stage. After measurements it was concluded that **input** devices always induced an initial value of '1'.

![](_page_20_Picture_0.jpeg)

![](_page_20_Picture_59.jpeg)

![](_page_20_Picture_60.jpeg)

![](_page_21_Picture_0.jpeg)

![](_page_21_Picture_2.jpeg)

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![](_page_22_Picture_0.jpeg)

![](_page_22_Picture_2.jpeg)

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![](_page_24_Picture_0.jpeg)

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![](_page_25_Picture_2.jpeg)

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- ▶ A new block called Power-on Reseted Flip-Flop (POR-FF) was designed and tested in CMOS 130nm, verifying its correct functioning.
- $\triangleright$  This technique has the advantage of avoiding power-on reset module and reset inputs in each sequential cell. (lower occupied area and lower dynamic power consumption)

![](_page_26_Picture_0.jpeg)

![](_page_26_Picture_1.jpeg)

![](_page_26_Picture_2.jpeg)